Translator, Dual Differential LVPECL to LVTTL

The NB100ELT23L is a dual differential LVPECL/LVDS to LVTTL translator. Because LVPECL (Positive ECL) or LVDS levels are used, only +3.3 V and ground are required. The small outline 8-lead package and the dual gate design of the ELT23L makes it ideal for applications which require the translation of a clock and a data signal.

The ELT23L is available in only the ECL 100K standard. Since there are no LVPECL outputs or an external V_{BB} reference, the ELT23L does not require both ECL standard versions. The LVPECL inputs are differential. Therefore, the NB100ELT23L can accept any standard differential LVPECL/LVDS input referenced from a V_{CC} of $\pm 3.3~V$.

Features

- 2.1 ns Typical Propagation Delay
- Maximum Operating Frequency > 160 MHz
- 24 mA LVTTL Outputs
- Operating Range: $V_{CC} = 3.0 \text{ V}$ to 3.6 V with GND = 0 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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MARKING DIAGRAMS*



SOIC-8 D SUFFIX CASE 751





TSSOP-8 DT SUFFIX CASE 948R



A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week

■ = Pb–Free Package

(Note: Microdot may be in either location)

*For additional marking information, refer to Application Note AND8002/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

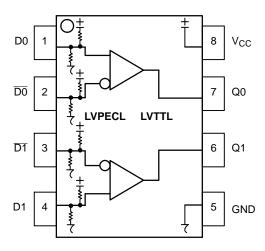


Figure 1. 8-Lead Pinout (Top View) and Logic Diagram

Table 1. PIN DESCRIPTION

PIN	FUNCTION
Q0, Q1	LVTTL Outputs
D0*, D1* D0**, D1**	Differential LVPECL Inputs
V _{CC}	Positive Supply
GND	Ground

^{*}Pins will default to $V_{\rm CC}/2$ when left open. If connected to a common termination voltage under no signal conditions, then the device will be susceptible to self–oscillation.

Table 2. ATTRIBUTES

Characteristi	cs	Value
Internal Input Pulldown Resistor	<u>D</u> D	50 kΩ 75 kΩ
Internal Input Pullup Resistor		50 kΩ
ESD Protection	Human Body Model Machine Model Charged Device Model	> 1.5 kV > 100 V > 2 kV
Moisture Sensitivity, Indefinite Time C	Out of Drypack (Note 1)	Pb-Free Pkg
	SO-8 TSSOP-8	Level 1 Level 3
Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 1.25 in
Transistor Count		91 Devices
Meets or exceeds JEDEC Spec EIA/	JESD78 IC Latchup Test	

^{1.} For additional information, see Application Note AND8003/D.

^{**}Pins will default to 2/3 $V_{\rm CC}$ when left open. If connected to a common termination voltage under no signal conditions, then the device will be susceptible to self–oscillation. See AND8020, Section 6 for options.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	Power Supply	GND = 0 V		3.8	V
VI	Input Voltage	GND = 0 V	$V_I \le V_{CC}$	3.8	V
l _{out}	Output Current	Continuous Surge		50 100	mA mA
T _A	Operating Temperature Range			-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SO-8 SO-8	190 130	°C/W
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	Standard Board	SO-8	41 to 44	°C/W
θ_{JA}	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8 TSSOP-8	185 140	°C/W
θ _{JC}	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
T _{sol}	Wave Solder Pb-Free	<2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Table 4. PECL DC CHARACTERISTICS V_{CC} = 3.3 V, GND = 0 V (Note 2)

			-40°C 25°C				85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I _{CCH}	Power Supply Current (Outputs set to HIGH)	10	23	30	10	23	30	10	24	30	mA
I _{CCL}	Power Supply Current (Outputs set to LOW)	15	26	35	15	26	35	15	27	35	mA
V _{IH}	Input HIGH Voltage	2075		2420	2075		2420	2075		2420	mV
V _{IL}	Input LOW Voltage	1355		1675	1355		1675	1355		1675	mV
V _{IHCMR}	Input HIGH Voltage Common Mode Range (Note 3)	1.2		3.3	1.2		3.3	1.2		3.3	V
I _{IH}	Input HIGH Current			150			150			150	μΑ
I _{IL}	Input LOW Current	-150			-150			-150			μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- All values vary 1:1 with V_{CC}.
 V_{IHCMR} minimum varies 1:1 with V_{EE}, V_{IHCMR} max varies 1:1 with V_{CC}. The V_{IHCMR} range is referenced to the most positive side of the differential input signal.

Table 5. TTL DC CHARACTERISTICS $V_{CC} = 3.3 \text{ V}$, GND = 0.0 V, $T_A = -40^{\circ}\text{C}$ to 85°C

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V _{OH}	Output HIGH Voltage	$I_{OH} = -3.0 \text{ mA}$	2.4			V
V _{OL}	Output LOW Voltage	I _{OL} = 24 mA			0.5	V
Ios	Output Short Circuit Current		-180		-50	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

Table 6. AC CHARACTERISTICS $V_{CC}\!=\,3.3~V~\pm\,5\%,\, \text{GND}=0.0~V~(\text{Note 4})$

			-40°C			25°C			85°C		
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f _{max}	Maximum Frequency	160			160			160			MHz
t _{PLH} , t _{PHL}	Propagation Delay to Output Differential (Note 5) $C_L = 20 \text{ pF}$	1.55	1.9	2.95	1.55	1.9	2.95	1.55	1.9	3.25	ns
t _{SK++} t _{SK} t _{SKPP}	Output-to-Output Skew++ Output-to-Output Skew Part-to-Part Skew (Note 6)			60 25 500			60 25 500			60 25 500	ps
t _{JITTER}	Random Clock Jitter (RMS)		6.0	20		6.0	20		6.0	20	ps
V_{PP}	Input Voltage Swing (Differential Configuration)	150	800	1200	150	800	1200	150	800	1200	mV
t _r t _f	Output Rise/Fall Times C _L = 20 pF (0.8 V to 2.0 V)	700 300	900	1700 1250	700 300	900	1700 1250	700 300	900	1700 1250	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

- 4. Measured using a 750 mV source, 50% duty cycle clock source. All loading with 500 Ω to GND, C_L = 20 pF.
- 5. Reference ($V_{CC} = 3.3 \text{ V} \pm 5\%$; GND = 0 V).
- 6. Skews are measured between outputs under identical conditions.

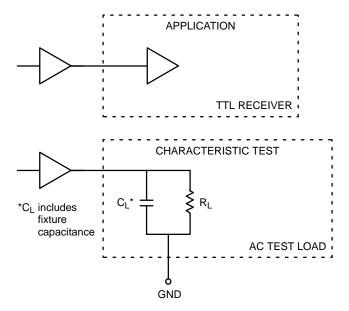


Figure 2. TTL Output Loading Used for Device Evaluation

ORDERING INFORMATION

Device	Package	Shipping [†]
NB100ELT23LDG	SO-8 (Pb-Free)	98 Units / Rail
NB100ELT23LDR2G	SO-8 (Pb-Free)	2500 / Tape & Reel
NB100ELT23LDTG	TSSOP-8 (Pb-Free)	100 Units / Rail
NB100ELT23LDTR2G	TSSOP-8 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Resource Reference of Application Notes

AN1405/D - ECL Clock Distribution Techniques

AN1406/D - Designing with PECL (ECL at +5.0 V)

AN1503/D - ECLinPS™ I/O SPiCE Modeling Kit

AN1504/D - Metastability and the ECLinPS Family

AN1568/D - Interfacing Between LVDS and ECL

AN1672/D – The ECL Translator Guide
AND8001/D – Odd Number Counters Design

AND8002/D - Marking and Date Codes

AND8020/D - Termination of ECL Logic Devices

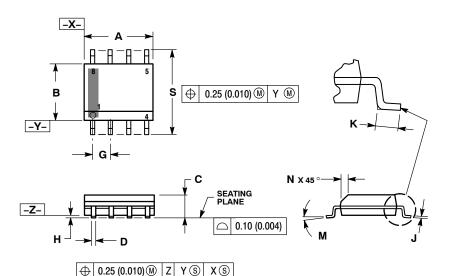
AND8066/D - Interfacing with ECLinPS

AND8090/D - AC Characteristics of ECL Devices



SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

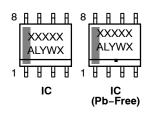
	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
M	0 °	0 ° 8 °		8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

SOLDERING FOOTPRINT*



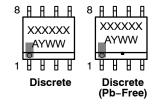
^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb–Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DHAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	0 COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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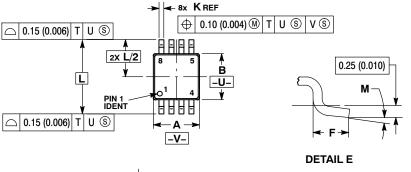


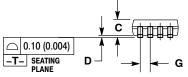
TSSOP 8 CASE 948R-02 ISSUE A

DETAIL E

DATE 04/07/2000

SCALE 2:1





- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH. OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD
- FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65	BSC	0.026 BSC	
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193 BSC	
М	0°	6 °	0°	6°

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